



Shantou Huashan Electronic Devices Co.,Ltd.

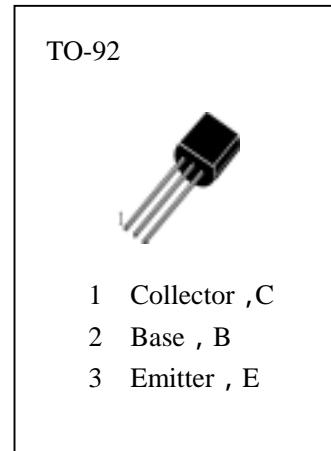
NPN SILICON TRANSISTOR

**H547**

## SWITCHING AND AMPLIFIER

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_C$ —Collector Dissipation.....	500mW
$V_{CBO}$ —Collector-Base Voltage.....	50V
$V_{CEO}$ —Collector-Emitter Voltage.....	45V
$V_{EBO}$ —Emitter-Base Voltage.....	6V
$I_C$ —Collector Current.....	100mA



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{CBO}$	Collector Cut-off Current			15	nA	$V_{CB}=30V, I_E=0$
$HFE(1)$	DC Current Gain	110		800		$V_{CE}=5V, I_C=2mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage		90	250	mV	$I_C=10mA, I_B=0.5mA$
$V_{CE(sat2)}$			200	600	mV	$I_C=100mA, I_B=5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage		0.7		V	$I_C=10mA, I_B=0.5mA$
$V_{BE(sat2)}$			0.9		V	$I_C=100mA, I_B=5mA$
$V_{BE(ON1)}$	Base-Emitter On Voltage	580	660	700	mV	$V_{CE}=5V, I_C=2mA$
$V_{BE(ON2)}$				720	mV	$V_{CE}=5V, I_C=10mA$
$f_T$	Current Gain-Bandwidth Product		300		MHz	$V_{CE}=5V, I_C=10mA$
NF	Noise Figure		2	10	dB	$V_{CE}=5V, I_C=200\mu A$ $f=1KHz, R_g=2K$

### $hFE$ Classification

A

B

C

110—220

200—450

420—800